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SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

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, BC869

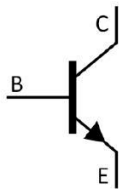
Low voltage, high current, Complementary to BC869.

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General purpose switching and amplification, such as audio output stages.

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PIN1 Base PIN 2 Collector PIN 3 Emitter

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Marking	HCAC*
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静态参数

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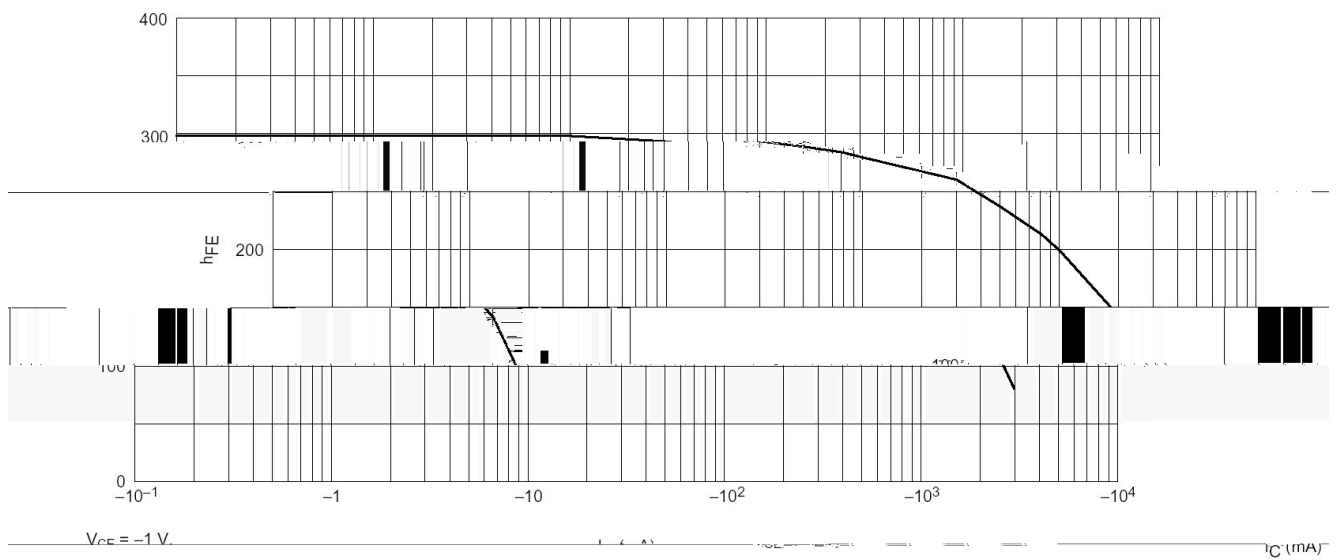
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	32	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current-Continuous	I_C	1.0	A
Peak Collector Current	I_{CM}	2.0	A
Peak Base Current	I_{BM}	200	mA
Collector Power Dissipation	P_C	1.35	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

交流参数

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Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=25V$ $I_E=0$			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=500mA$	85		375	
	$h_{FE(2)}$	$V_{CE}=10V$ $I_C=5.0mA$	50			
	$h_{FE(3)}$	$V_{CE}=1.0V$ $I_C=1.0A$	60			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.0A$ $I_B=100mA$			500	mV
Base to Emitter Voltage	$V_{BE(1)}$	$V_{CE}=10V$ $I_C=5.0mA$		620		mV
	$V_{BE(2)}$	$V_{CE}=1.0V$ $I_C=1.0A$			1.0	V
Transition Frequency	f_T	$V_{CE}=5.0V$ $f=100MHz$ $I_C=10mA$	40			MHz

静态特性



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SOT-89

单位: mm

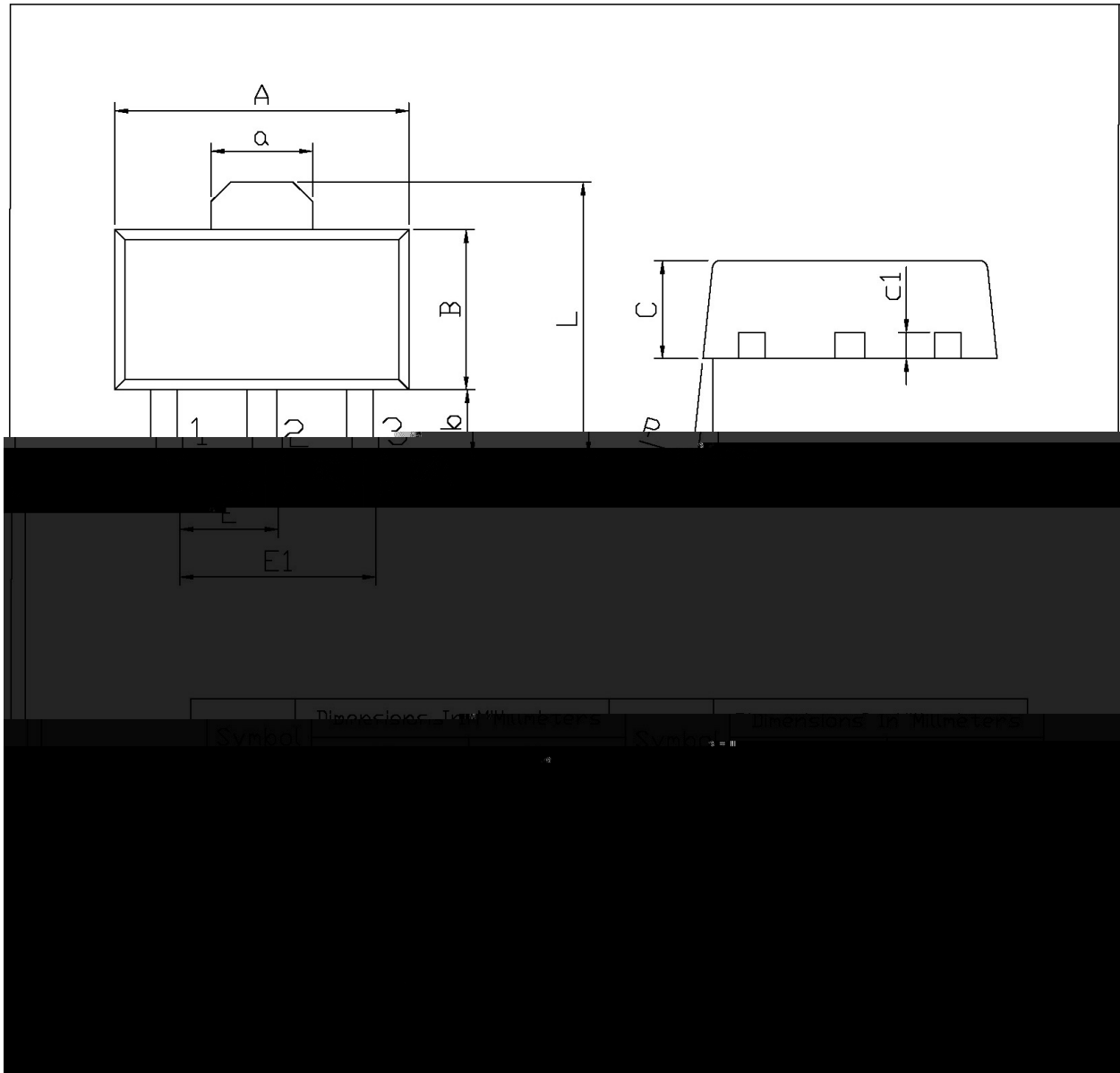
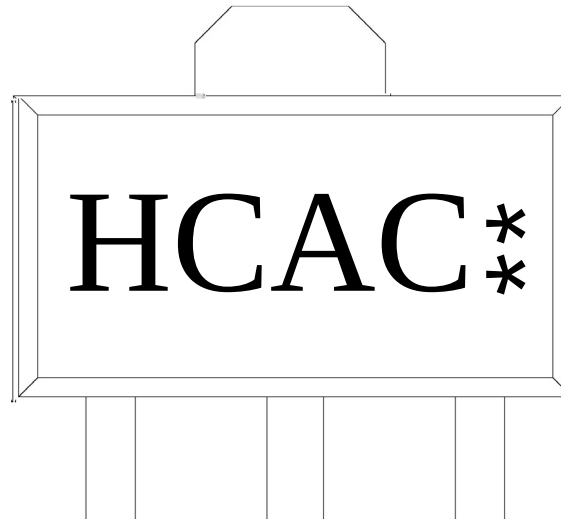


图 2



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CAC

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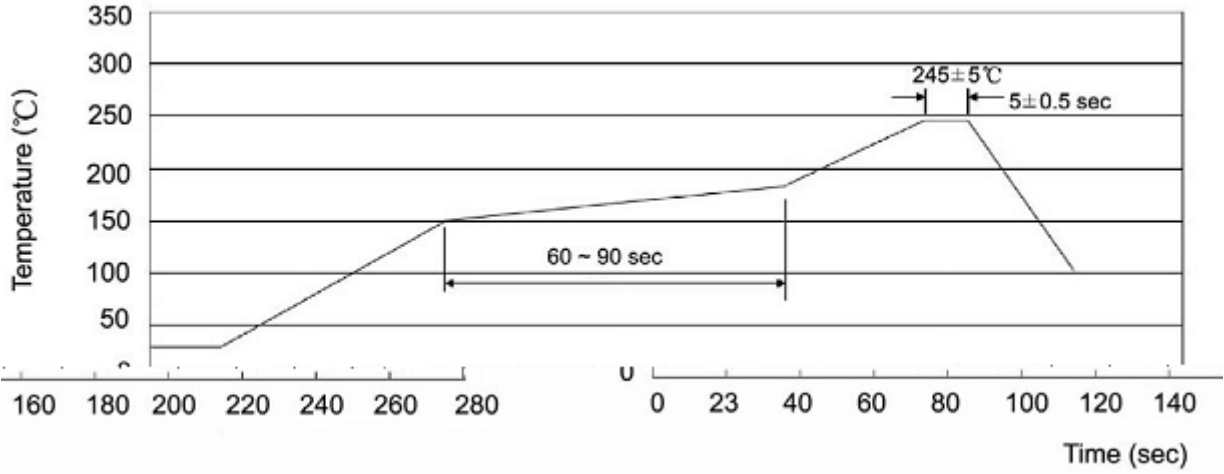
Note:

H: Company Code.

CAC: Product Type.

** : Lot No. Code, code change with Lot No.

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- Note:
1. Preheating: 25~150 , Time: 60~90sec.

2. Peak Temp.: 245±5 , Duration: 5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec. Temp.: 260±5°C Time: 10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱

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